

# Forward Silicon Tracker (FSD) status

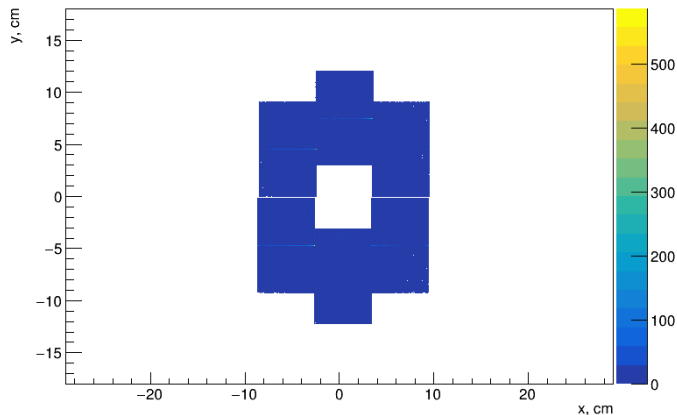
Oleg Tarasov on behalf of Forward Silicon Tracker team

**12th Collaboration Meeting of the BM@N Experiment at the NICA Facility  
May 13 – 17, 2024**

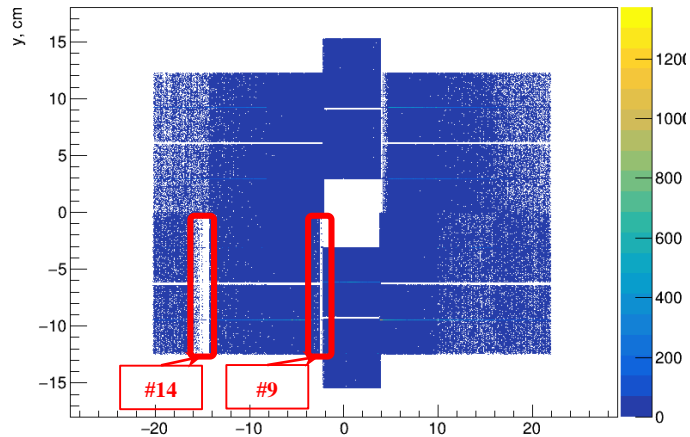
## Content of the report:

- 1 Diagnostics and elimination of defects in FSD-planes.
- 2 Coordinates of modules (Si-detectors) after disassembly-assembly of FSD-planes.
- 3 Refinement of FSD-planes positioning device in the BM@N experimental hall.
- 4 Conclusion.

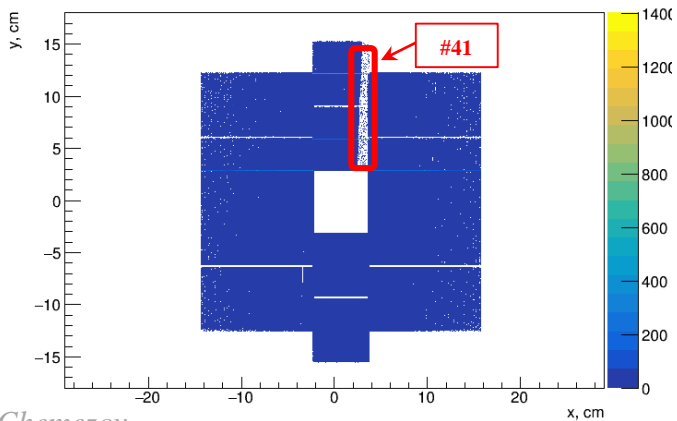
Hits on station 1  
6 modules, DSSD 63×93 mm<sup>2</sup>



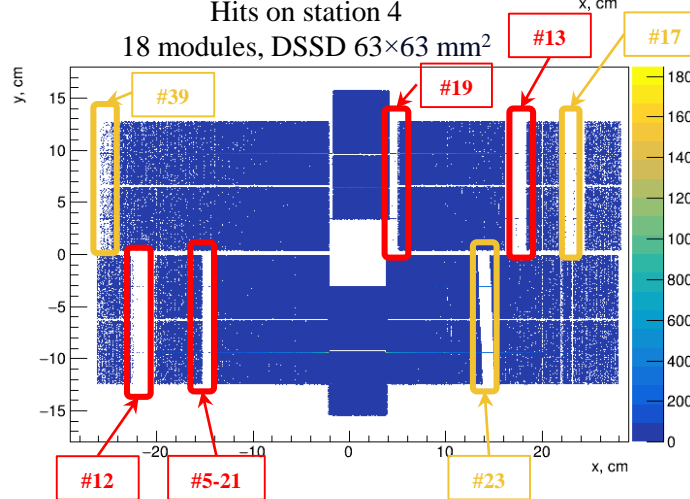
Hits on station 3  
14 modules, DSSD 63×63 mm<sup>2</sup>



Hits on station 2  
10 modules, DSSD 63×63 mm<sup>2</sup>



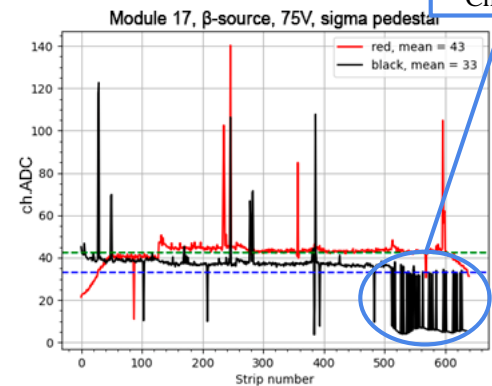
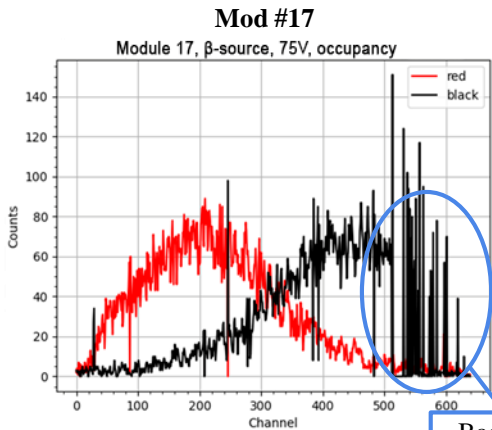
Hits on station 4  
18 modules, DSSD 63×63 mm<sup>2</sup>



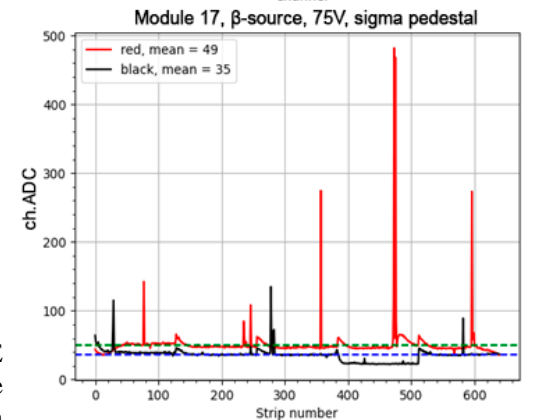
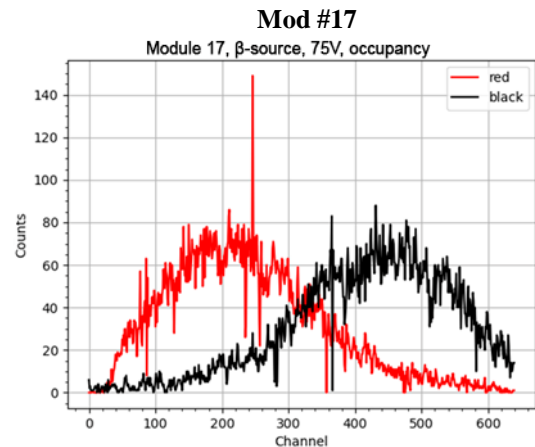
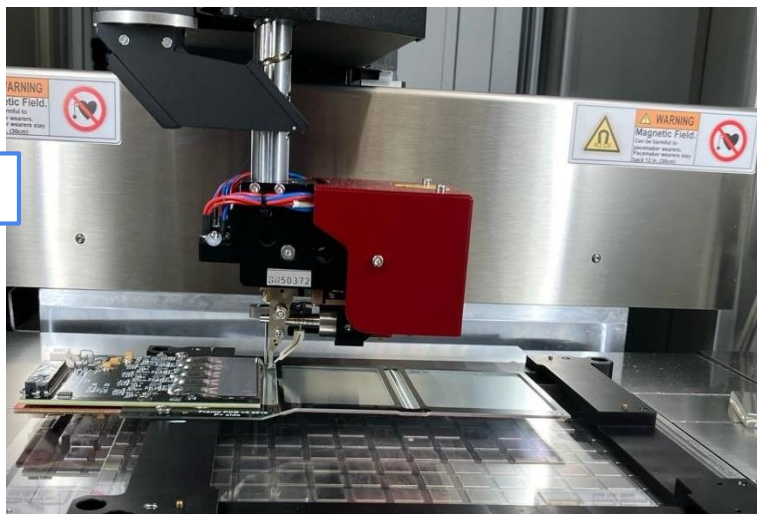
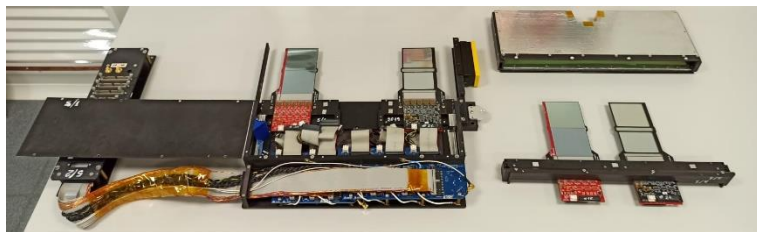
Run	8305
Beam	Xe
Energy	3.8 GeV/n
Target	Csl (2%)

Summary:  
10 dead zones, 3 were discovered before the run and 7 occurred during the run

Module	Chip
#41	5Y
#14	5X
#9	5X
#39	1X
#19	5X
#13	4X, 5X
#17	4X, 5X
#12	4X, 5X
#5-21	5X
#23	4Y

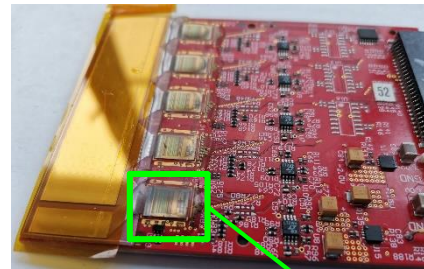
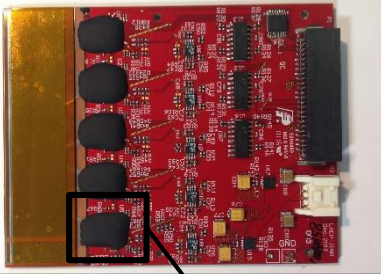


Bad zone  
Chip #5



After replacement

To eliminate the dead zones it was necessary to assemble a new FEE board completely, 5 ASICs were spent to eliminate each of defects. The old boards were disconnected from the modules and replaced with a new ones. Total: 9 new black boards (p+ strips) were built, 45 VATAGP 7.2 ASICs were used (30 spare ASICs available).



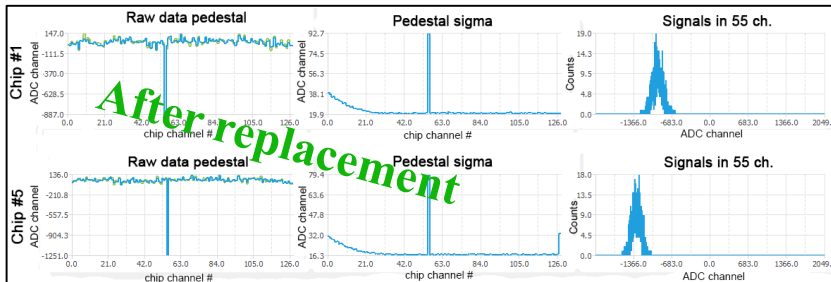
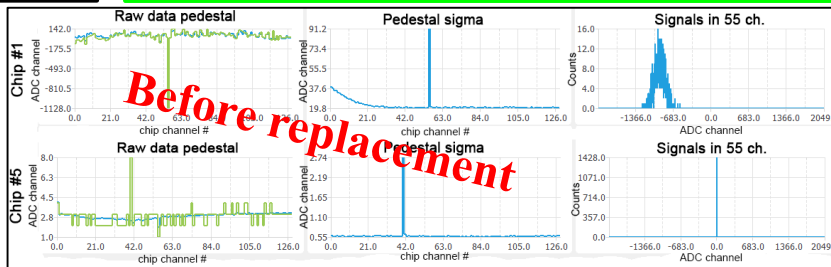
- Black **BE-08** encapsulant (polarization temperature 100°C)
- an additional optical shield for chips
  - **Not removable** mechanically or with chemical solvents (dimethyl sulfoxide, dimethylformamide, CH<sub>2</sub>O<sub>2</sub>)

- Ultra Light-Weld 9008 Flexible, UV-Curable Encapsulant
- Does not create an additional optical shield
  - Can be mechanically removed so **FEE boards are repairable**

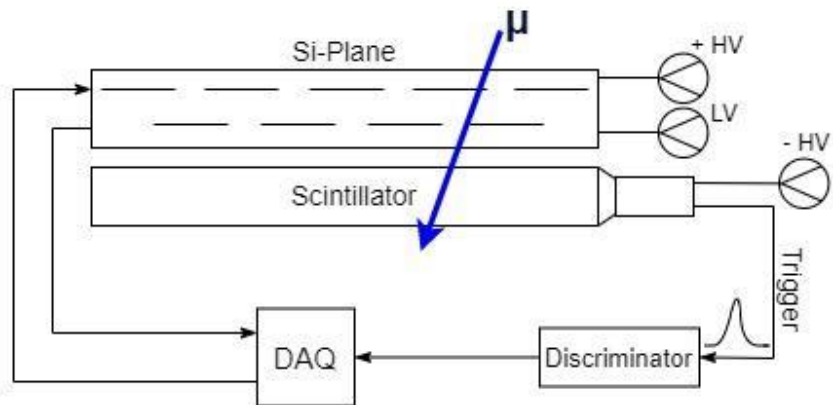
Replacement of one chip:



removed chip

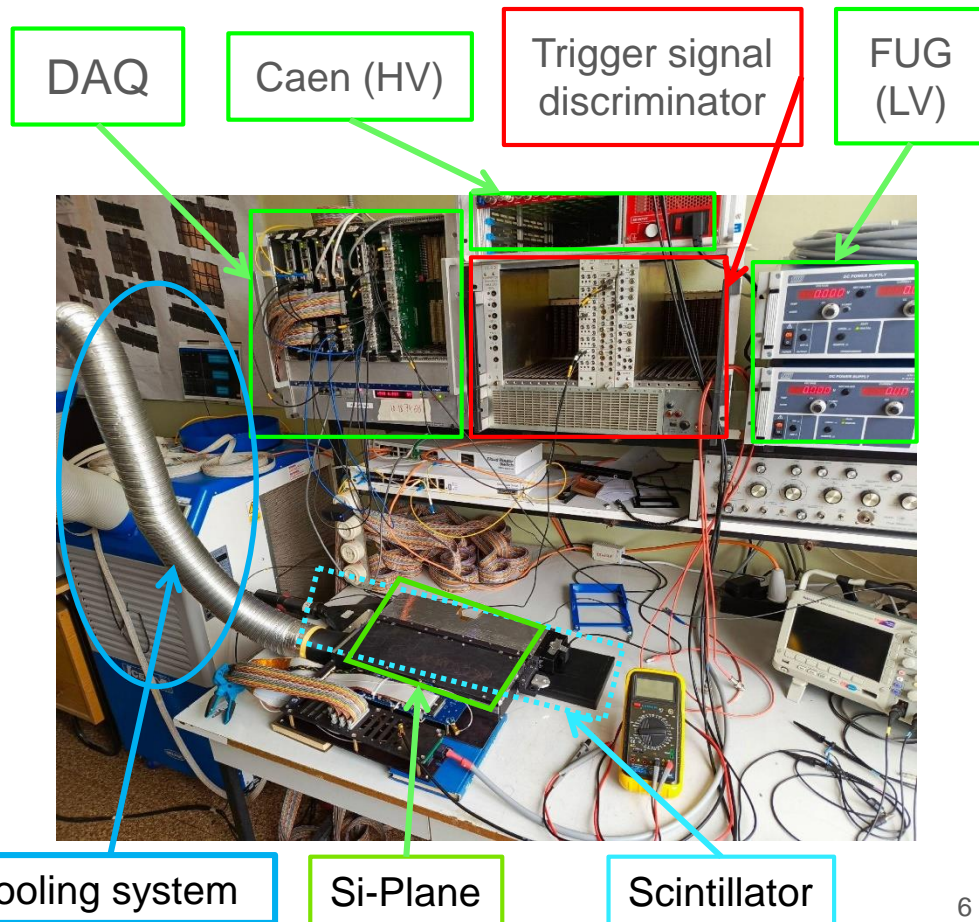






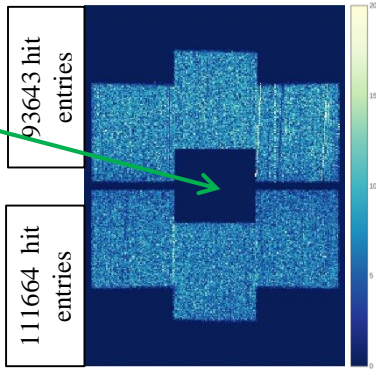
Dimensions:

- Scintillator: 150x600 mm<sup>2</sup>
- Station-1, half-plane: 93x180 mm<sup>2</sup>
- Station-2, half-plane: 126x300 mm<sup>2</sup>
- Station-3, half-plane: 126x420 mm<sup>2</sup>
- Station-4, half-plane: 126x540mm<sup>2</sup>

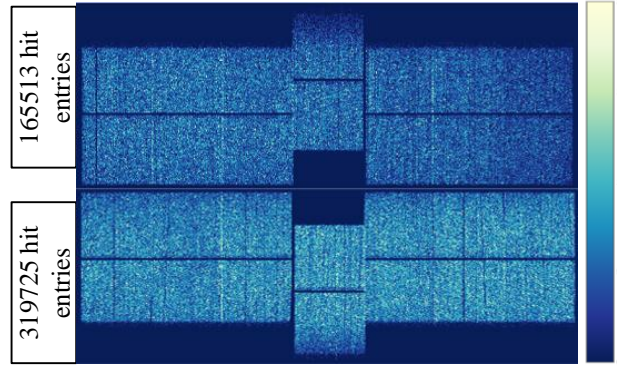


Cosmic tests station 1

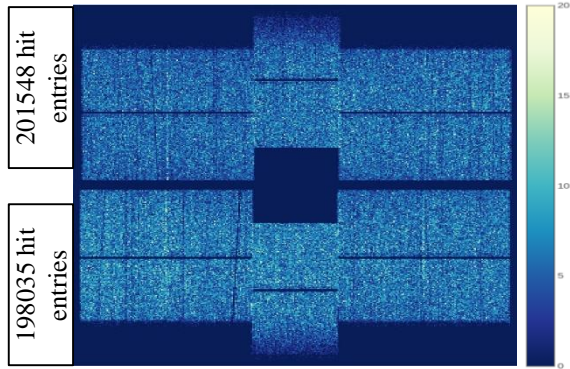
Beam hole



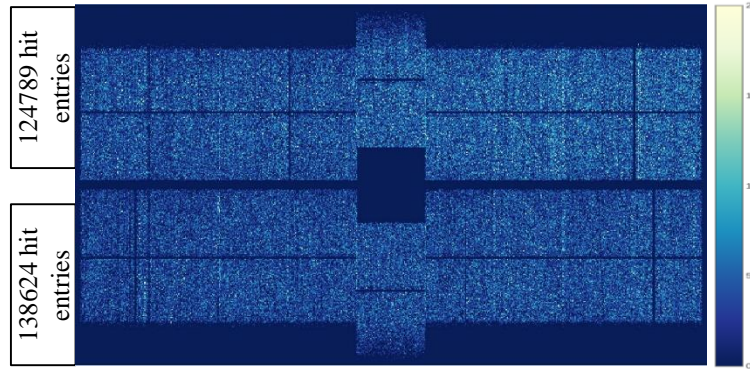
Cosmic tests station 3



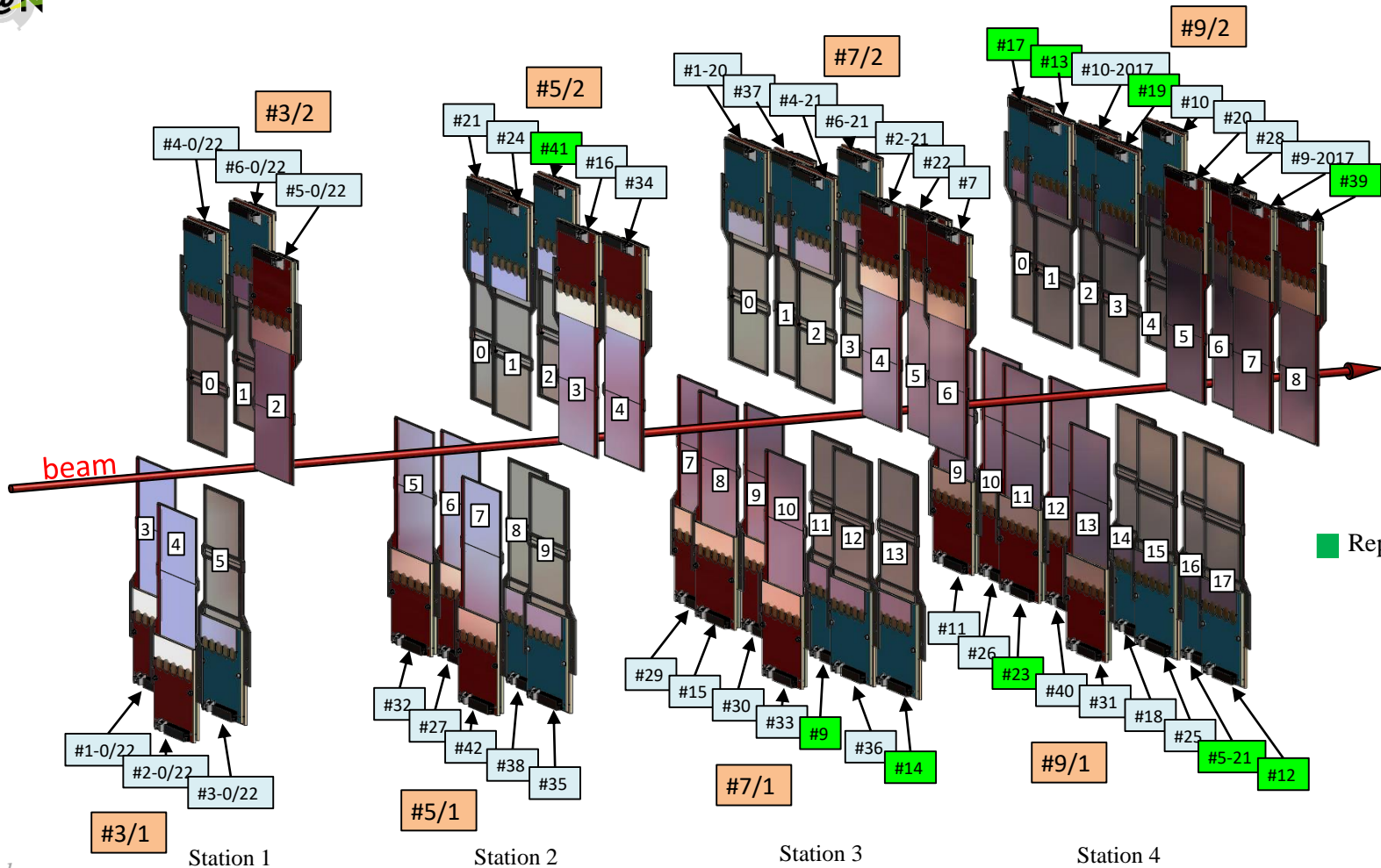
Cosmic tests station 2



Cosmic tests station 4

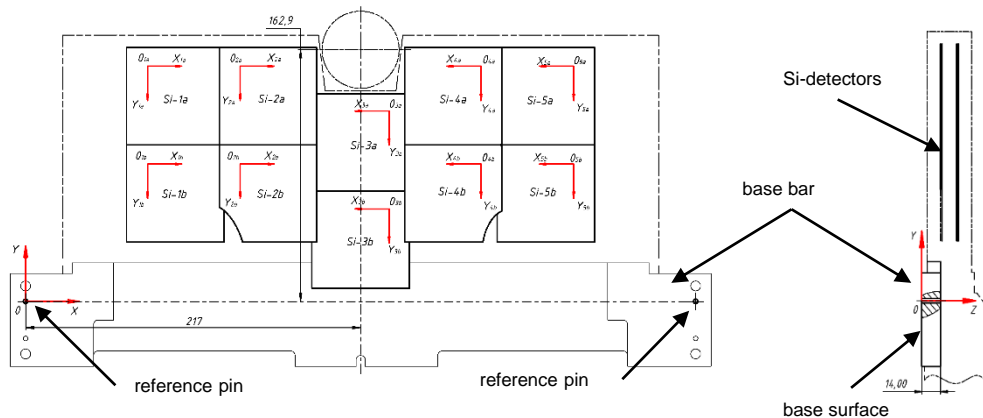


All dead zones have been eliminated!



Repaired modules (10 pcs)





Position of Si-sensors in half-plane # 5/2 (25.03.24) after repair

Sensor position	$X \pm 0.02^*$ (mm)	$Y \pm 0.02^*$ (mm)	Turn in OXY plane (deg.)**	$Z \pm 0.2^{***}$ (mm)	Module serial number
Si-1a	65.55	164.23	-0.03	16.0	#34
Si-1b	65.59	101.25	0.01	15.7	
Si-2a	125.45	164.21	0.04	27.6	#16
Si-2b	125.55	101.26	-0.01	27.6	
Si-3a	248.63	134.21	-0.04	14.0	#41 repair
Si-3b	248.57	71.22	-0.03	13.9	
Si-4a	308.42	164.24	-0.01	25.8	#24
Si-4b	308.46	101.26	0.0	25.9	
Si-5a	368.64	164.25	-0.06	14.2	#21
Si-5b	368.56	101.26	-0.03	14.0	

Difference in Si-sensors position data in half-plane # 5/2 (25.03.24 compared to 06.07.22)

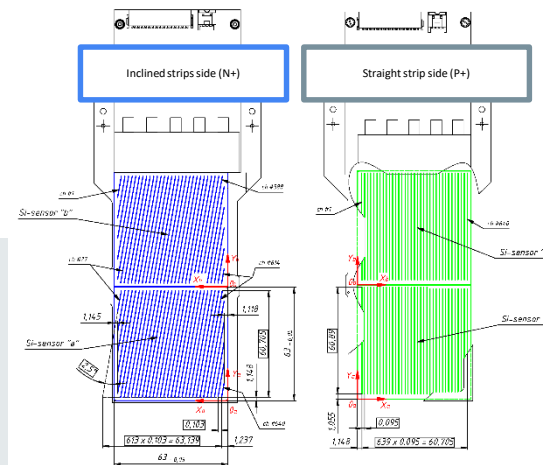
Sensor position	$\Delta X$ (mm)	$\Delta Y$ (mm)	Changin of turn (deg.)**	$\Delta Z$ (mm)	Module serial number
Si-1a	-0.08	-0.02	0.0	0.1	#34
Si-1b	-0.05	-0.01	0.0	0.0	
Si-2a	-0.09	-0.02	0.0	0.1	#16
Si-2b	-0.06	0.0	0.0	0.1	
Si-3a	-0.06	-0.02	-0.02	-0.5	#41 repair
Si-3b	-0.03	-0.01	0.0	-0.3	
Si-4a	-0.08	-0.01	0.0	-0.3	#24
Si-4b	-0.05	0.0	0.0	-0.1	
Si-5a	-0.07	-0.02	0.01	-0.2	#21
Si-5b	-0.05	-0.01	0.0	-0.2	

Changing of Si-sensors positions after disassembly and reassembly does not exceed:

- 100  $\mu\text{m}$  for X-coordinate
- 50  $\mu\text{m}$  for Y-coordinate

\*-position of the origin point of the Si-sensors in the coordinate plane OXY (tied to the outer reference pins).

\*\*-the distance from the base surface of the base bar to the middle of the Si-sensors surface farthest from it.



Position of Si-sensors in plane # 5/2 (25.03.24) after repair

Sensor position	X±0.02* (mm)	Y±0.02* (mm)	Turn in OXY plane (deg.)**	Z±0.2*** (mm)	Module serial number
Si-1a	65.55	164.23	-0.03	16.0	#34
Si-1b	65.59	101.25	0.01	15.7	
Si-2a	125.45	164.21	0.04	27.6	#16
Si-2b	125.55	101.26	-0.01	27.6	
Si-3a	248.63	134.21	-0.04	14.0	#41 repair
Si-3b	248.57	71.22	-0.03	13.9	
Si-4a	308.42	164.24	-0.01	25.8	#24
Si-4b	308.46	101.26	0.0	25.9	
Si-5a	368.64	164.25	-0.06	14.2	#21
Si-5b	368.56	101.26	-0.03	14.0	

Position of Si-sensors in plane # 7/1 (27.03.24) after repair

Sensor position	X±0.02* (mm)	Y±0.02* (mm)	Turn in OXY plane (deg.)**	Z±0.2*** (mm)	Module serial number
Si-1a	65.47	164.14	0.03	28.6	#14 repair
Si-1b	65.48	101.11	0.04	28.0	
Si-2a	125.39	164.27	0.06	16.2	#36
Si-2b	125.48	101.29	0.05	15.8	
Si-3a	185.42	164.13	0.05	28.0	#9 repair
Si-3b	185.47	101.12	0.04	27.8	
Si-4a	308.46	134.28	-0.04	14.2	#33
Si-4b	308.41	71.31	0.03	14.0	
Si-5a	368.43	164.21	0	25.8	#30
Si-5b	368.41	101.21	0.02	26.1	
Si-6a	428.48	164.27	-0.02	14.5	#15
Si-6b	428.46	101.27	-0.01	14.2	
Si-7a	488.57	164.18	-0.06	25.7	#29
Si-7b	488.50	101.18	-0.06	26.0	

Position of Si-sensors in plane # 9/1 (10.04.24) after repair

Sensor position	X±0.03* (mm)	Y±0.05* (mm)	Turn in OXY plane (deg.)**	Z±0.2*** (mm)	Module serial number
Si-1a	65.46	164.28	0.03	15.0	#12 repair
Si-1b	65.59	101.21	0.05	15.3	
Si-2a	125.48	164.31	0.04	26.4	#5-21 repair
Si-2b	125.56	101.18	0.02	27.2	
Si-3a	185.54	164.36	0.01	15.2	#25
Si-3b	185.60	101.35	0.00	15.3	
Si-4a	245.39	164.34	0.06	26.7	#18
Si-4b	245.50	101.13	0.06	27.2	
Si-5a	368.46	134.37	-0.02	14.4	#31
Si-5b	368.48	71.37	0.01	14.0	
Si-6a	428.42	164.35	0.00	25.8	#40
Si-6b	428.48	101.35	0.01	25.9	
Si-7a	488.61	164.35	-0.03	13.7	#23 repair
Si-7b	488.59	101.34	-0.05	13.7	
Si-8a	548.45	164.37	0.01	25.7	#26
Si-8b	548.49	101.38	0.01	25.8	
Si-9a	608.60	164.32	-0.04	14.7	#11
Si-9b	608.60	101.29	-0.02	14.3	

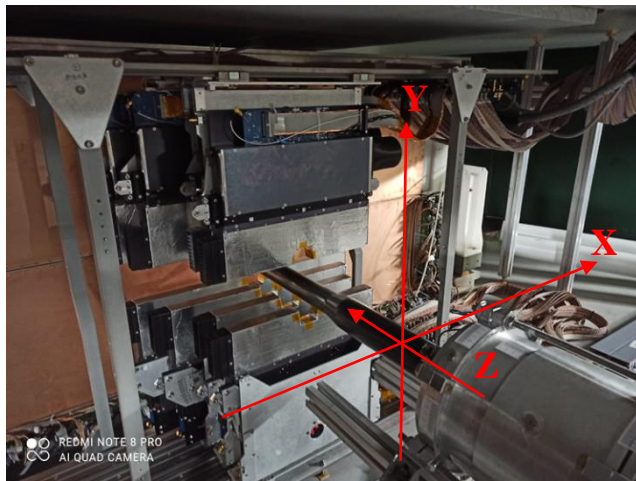
Position of Si-sensors in plane # 9/2 (17.04.24) after repair

Sensor position	X±0.03* (mm)	Y±0.05* (mm)	Turn in OXY plane (deg.)**	Z±0.2*** (mm)	Module serial number
Si-1a	65.58	164.27	0.01	16.2	#39 repair
Si-1b	65.59	101.28	0	15.8	
Si-2a	125.45	164.23	0.05	27.2	#9-2017
Si-2b	125.49	101.11	0.04	27.4	
Si-3a	185.41	164.22	0.07	16.2	#28
Si-3b	185.49	101.22	0.06	15.9	
Si-4a	245.51	164.29	0.03	27.8	#20
Si-4b	245.53	101.28	0.01	27.7	
Si-5a	368.44	134.32	0.01	14.1	#10
Si-5b	368.43	71.32	0.02	13.9	
Si-6a	429.39	164.32	0.01	26.5	#19 repair
Si-6b	428.39	101.33	0.02	26.2	
Si-7a	488.58	164.31	-0.06	14.5	#10-2017
Si-7b	488.51	101.30	-0.04	14.2	
Si-8a	548.50	164.31	-0.01	25.9	#13 repair
Si-8b	548.47	101.29	-0.01	25.9	
Si-9a	608.62	164.29	-0.07	14.2	#17 repair
Si-9b	608.54	101.28	-0.04	14.0	

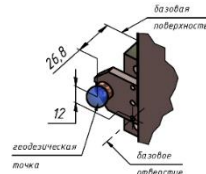
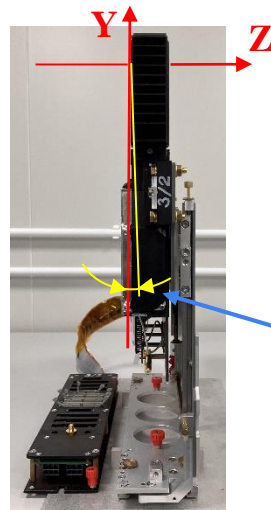
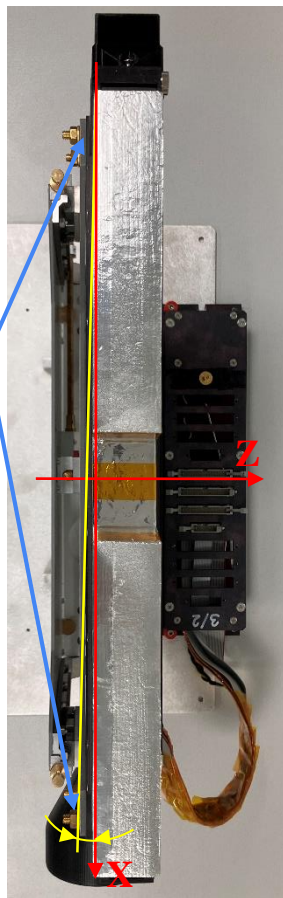


Measurement of Si-detectors position coordinates in 2024 were carried out on a new tooling for plane fixation on the table of video-measuring microscope "NORGAU" NVM II-5040D (3 points of support).

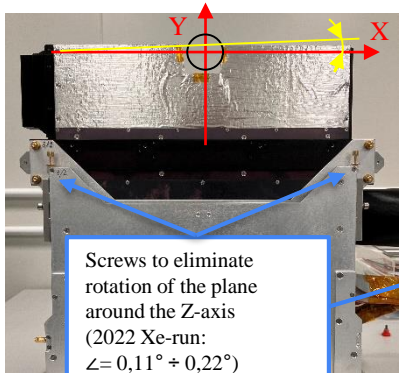
- New coordinates were entered into the data table for positions of detectors in FSD-planes



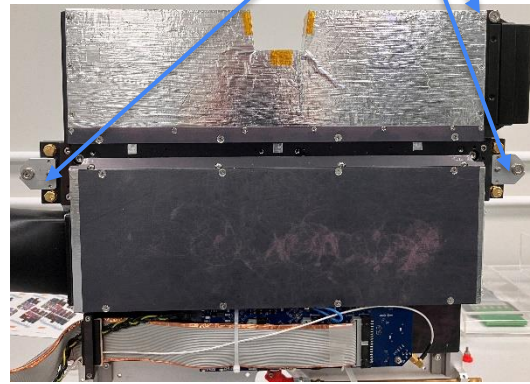
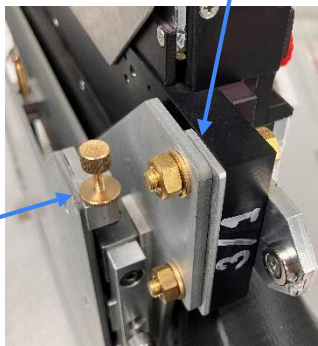
Adjustment shims to eliminate plane rotation around the Y axis.  
(2022 Xe-run:  
 $\angle = 0,11^\circ \pm 0,74^\circ$ )



Added a 3rd geodetic marker to control the inclination of the plane around the X axis



Screws to eliminate rotation of the plane around the Z-axis  
(2022 Xe-run:  
 $\angle = 0,11^\circ \pm 0,22^\circ$ )



## Conclusion

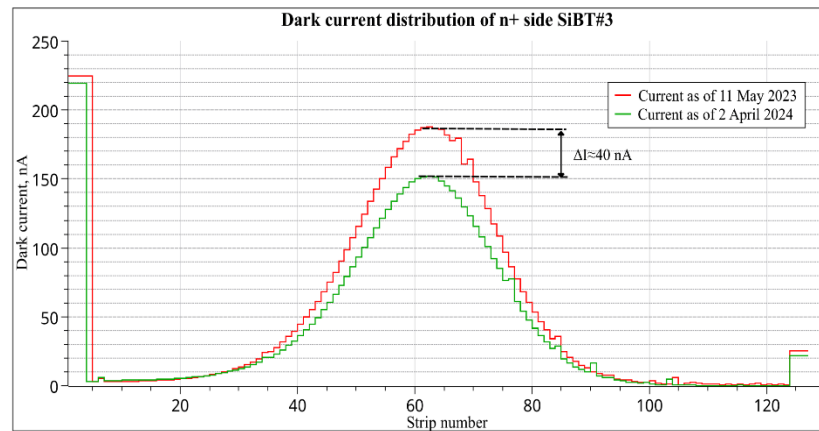
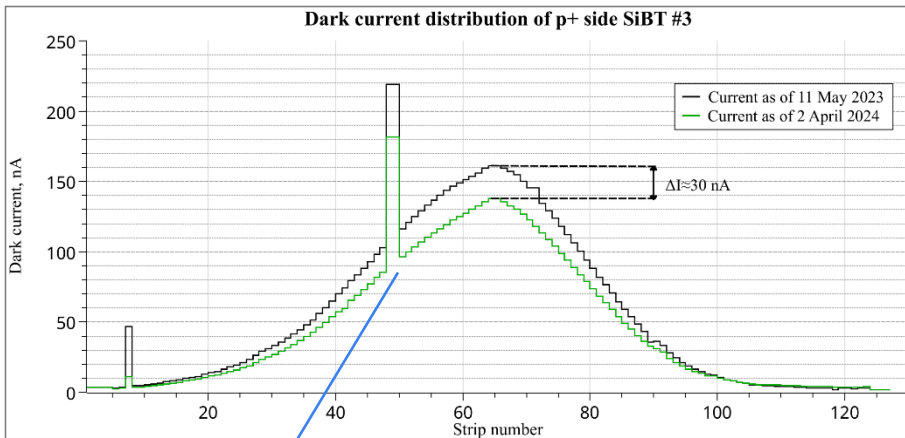
- Eliminated defects in FSD-planes, all defects were related to FEE-chips failures. At the end of Xe-run (February 2023) number of problematic chips were 2,7% (from 480 pC.), at the moment - 0%.
- FSD-planes are ready to installation and alignment in BM@N experimental hall .
- True coordinates of Si-detectors in FSD half-planes after disassembly-assembly during defects repair were measured with accuracy  $\pm 50\mu\text{m}$ .
- Refined FSD-planes positioning devices for alignment in BM@N experimental hall (added a 3-rd geodetic marker).



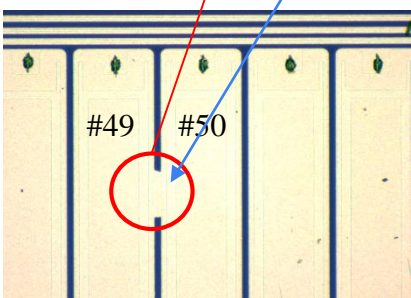
**Thank you for your attention!**



Additional slides



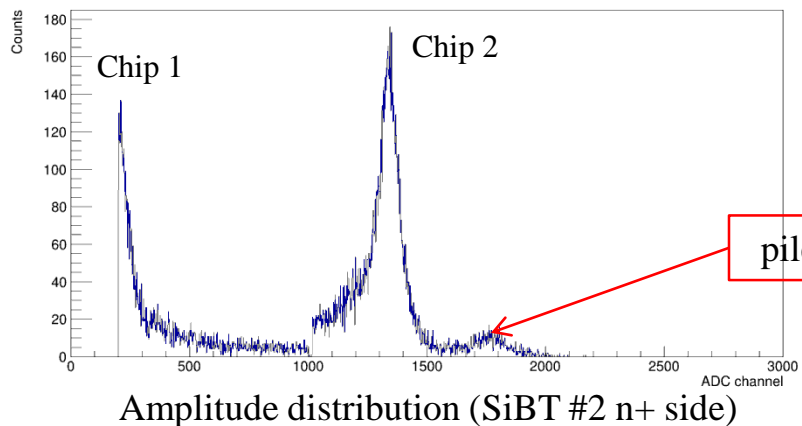
49 and 50th strips are shorted out on the detector. Irreparable defect



There was no contact on the connector. The defect was eliminated by cleaning the connectors

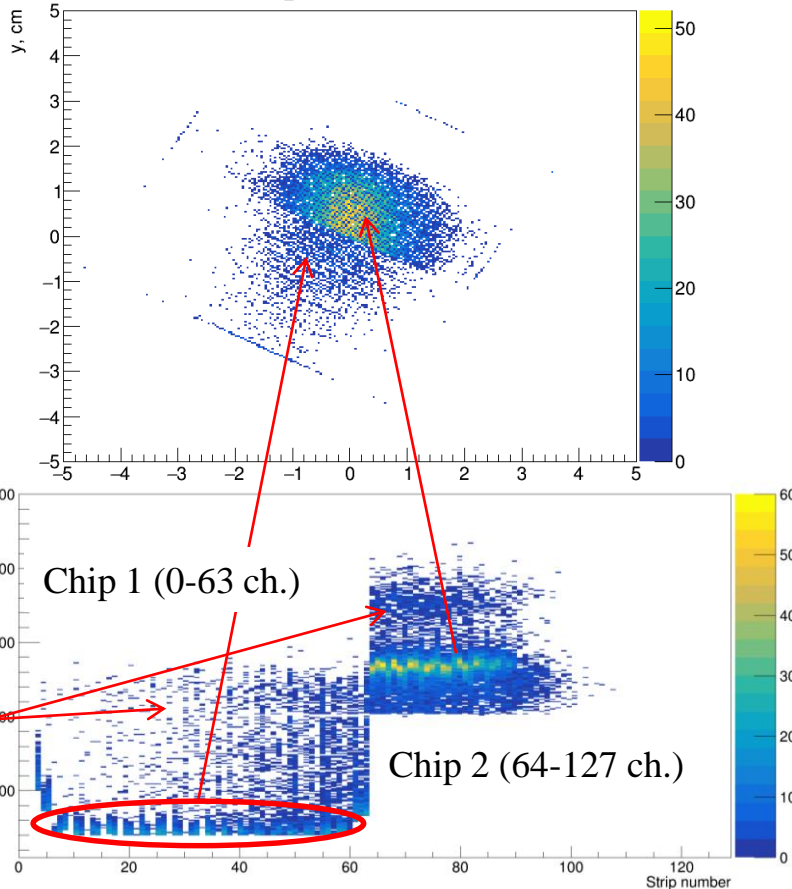
	$I_{max}, nA$	$I_{\Sigma}, \mu A$
May 2023	182	7.1
April 2024	219	5.9
Delta	≈40	1.2

This slide shows SiBT FEE operation in XE-run on example of SiBT #2 (run 8387, 1.02.2023). The gains of FEE-chips on n+ side were not tuned for signals on the order of 10.9 pC (energy losses of Xe with energy 3.8 GeV/n are 245.5 MeV). Because of this signals from one of FEE-chips were below th threshold and were not written (in this case – chip 1 (channels 0 – 63))



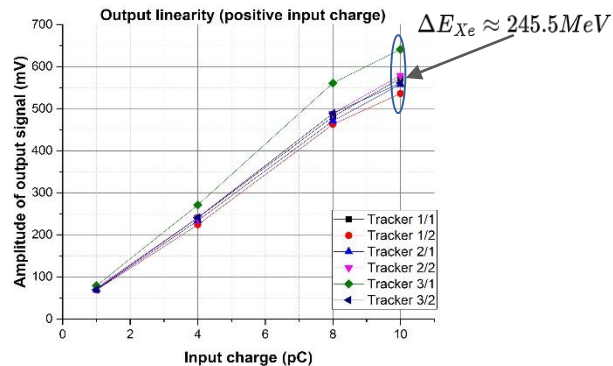
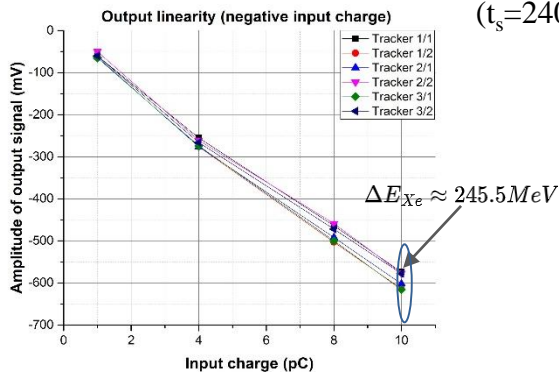
pileups

## Hit plot SiBT #2

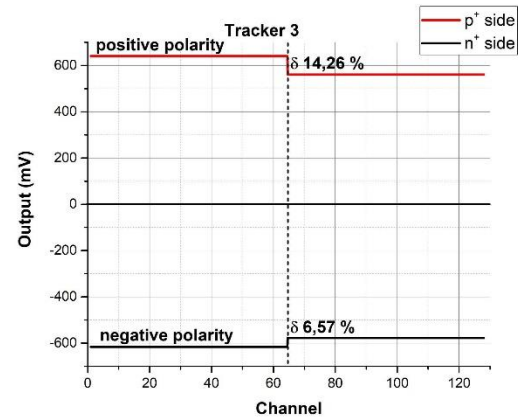
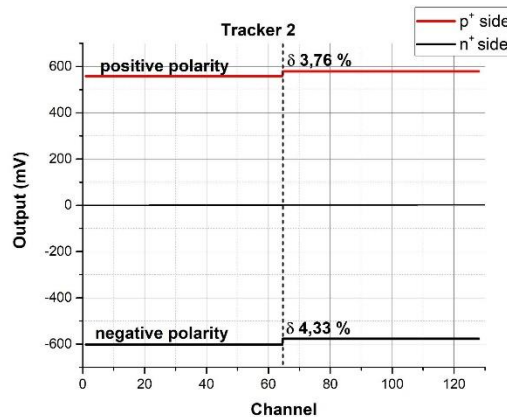
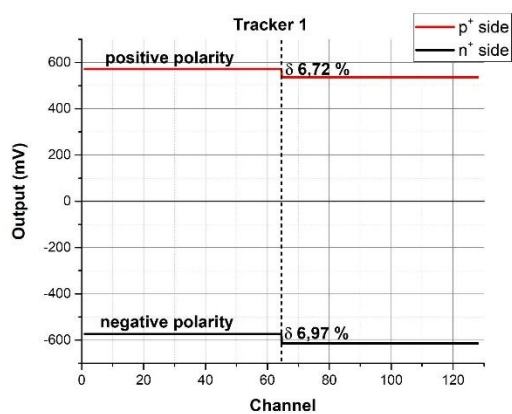


## Linearity of ASICs after PCB tuning

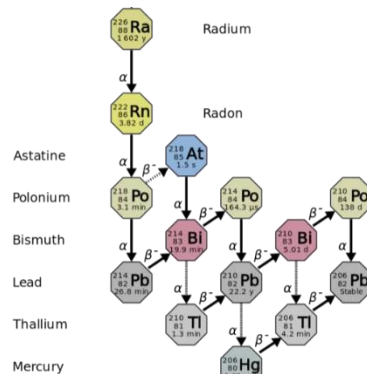
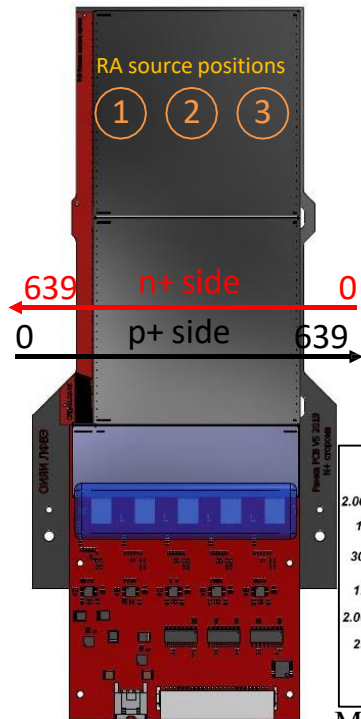
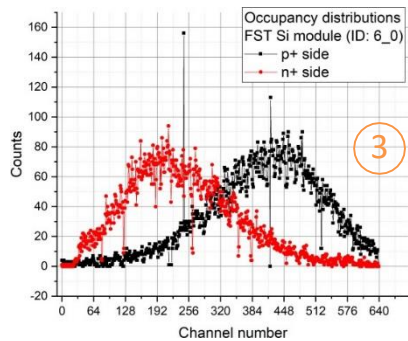
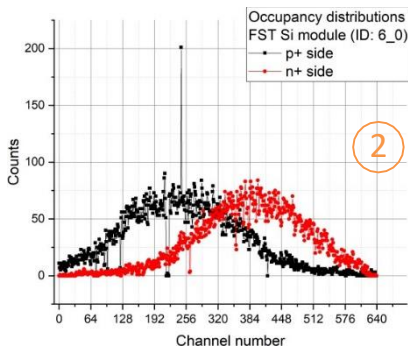
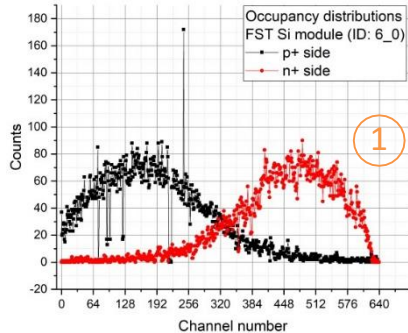
( $t_s=240$  ns)



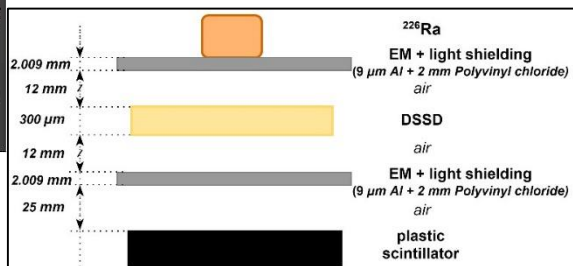
## The gain spread of ASICs (input 10 pC, $t_s=240$ ns+120 ns)



# FST Si module test results

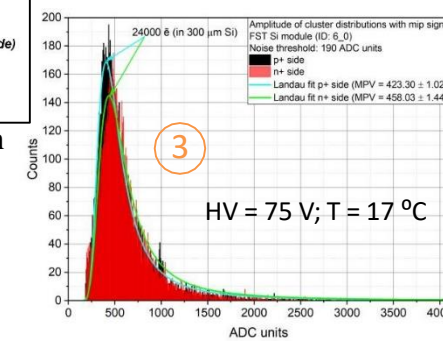
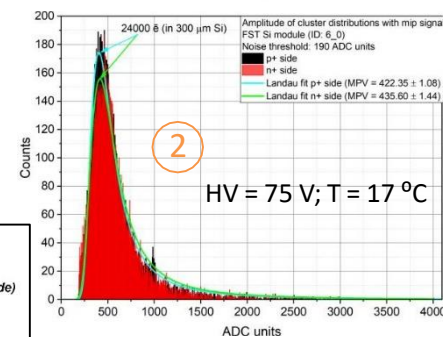
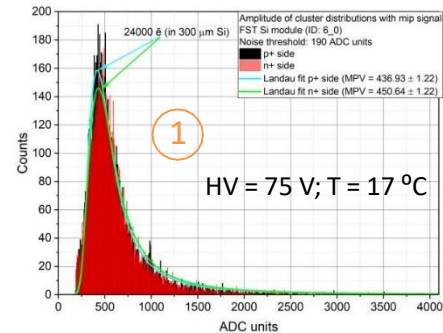


Electron end-point energy up to 3.27 MeV ( $^{214}_{83}\text{Bi}$ )



Measurement with RA source cross-section  
(trigger rate: 150 Hz)

Module ID	<ENCp+> $\bar{e}$ RMS	<ENCn+> $\bar{e}$ RMS	SNR p+ side	SNR n+ side	Bad channel s ratio, %
6_0	1963.60	2 237.88	12.22	10.72	1.25



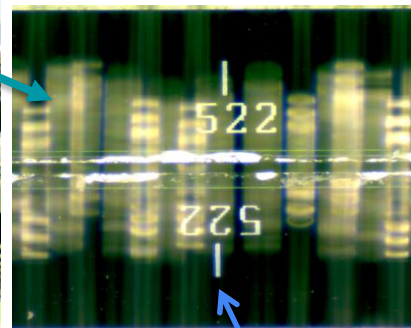
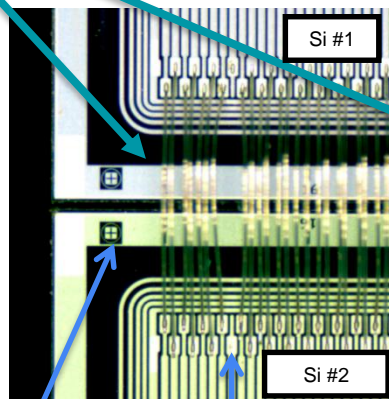


Измерения положения Si-детекторов в модулях и плоскостях проводились на бесконтактном видеоизмерительном микроскопе «NORGAU» NVM II-5040D.



«NORGAU» NVM II-5040D	
Диапазон перемещений по осям X и Y (мм)	500 x 400
Диапазон перемещений по оси Z (мм)	250
Допускаемая абсолютная погрешность линейных измерений по осям X и Y (мкм)*	$\pm(2.5+L/200)$
Допускаемая абсолютная погрешность линейных измерений по оси Z (мкм)*	$\pm(2.5+L/100)$

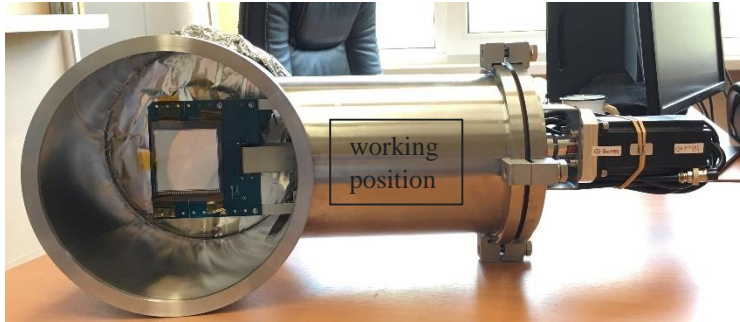
\* L –измеряемая длина в мм



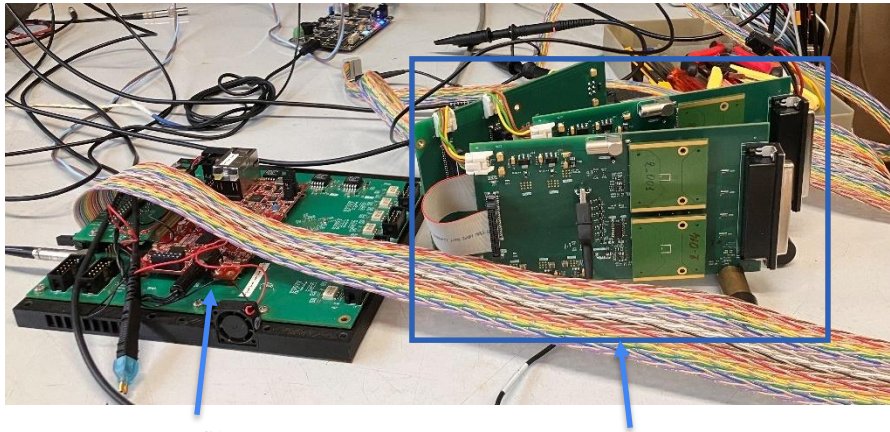
реперный крест детектора

отсутствие сварки

Топологические знаки на детекторе можно использовать в качестве реперов



Beam tracker Cross-board

Beam profilometer  
standalone DAQ

New readout electronics for beam profilometer

## Beam profilometer

is necessary for beam tuning (alignment of the center beam with the center of the target)

- **detector:** DSSD, ( $128p^+ \times 128n^+$ ), strips pitch =  $475 \mu\text{m}$ , thickness (Si) -  $175 \mu\text{m}$ , active area ( $61 \times 61$ )  $\text{mm}^2$ . Strips are combined in pairs on detector board. Total have ( $64p^+ \times 64n^+$ ), pitch =  $950 \mu\text{m}$
- **mechanical design:** the plane of the profilometer is automatically removed from the beam zone to the parking position
- **FEE** based on two VA32HDR11 ASICs. Total number of channels are 64 for X and 64 for Y coordinate. Dynamic range  $-35\text{pC} - +25\text{pC}$ . Peaking time 800ns. Self trigger mode based on TA32cg2 ASICs
- **current status:**  
FEE have been designed, manufactured and tested. Next step is testing FEE with Si detector placed in flanges with alpha-source (5.5 MeV) and standalone DAQ subsystem.